

PNZ126S

Silicon NPN Phototransistor

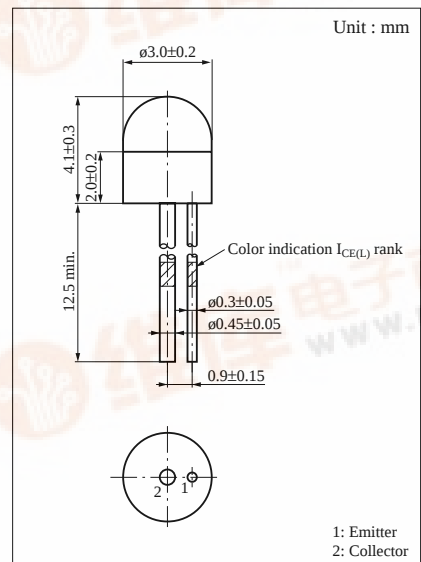
For optical control systems

Features

- High sensitivity
- Good collector photo current linearity with respect to optical power input
- Fast response : $t_r = 2.5 \mu s$ (typ.)
- Small size ($\phi 3$) ceramic package

Absolute Maximum Ratings ($T_a = 25^\circ C$)

Parameter	Symbol	Ratings	Unit
Collector to emitter voltage	V_{CEO}	20	V
Emitter to collector voltage	V_{ECO}	5	V
Collector current	I_C	20	mA
Collector power dissipation	P_C	50	mW
Operating ambient temperature	T_{opr}	-25 to $+85$	$^\circ C$
Storage temperature	T_{stg}	-30 to $+100$	$^\circ C$

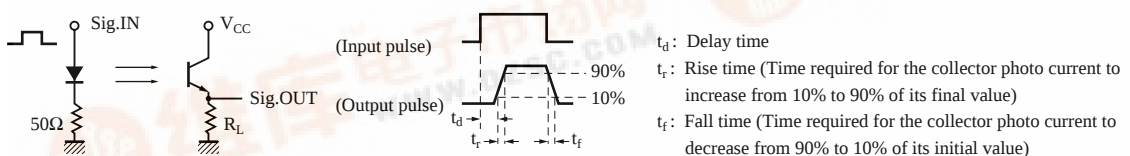


Electro-Optical Characteristics ($T_a = 25^\circ C$)

Parameter	Symbol	Conditions	min	typ	max	Unit
Dark current	I_{CEO}	$V_{CE} = 10V$		1	100	nA
Collector photo current	$I_{CE(L)}^{*3}$	$V_{CE} = 10V, L = 1000 \text{ lx}^{*1}$	1050		2560	μA
Peak sensitivity wavelength	λ_p	$V_{CE} = 10V$		800		nm
Acceptance half angle	θ	Measured from the optical axis to the half power point		30		deg.
Rise time	t_r^{*2}	$V_{CC} = 10V, I_{CE(L)} = 1mA, R_L = 100\Omega$		2.5		μs
Fall time	t_f^{*2}			3.5		μs

^{*1} Measurements were made using a tungsten lamp (color temperature $T = 2856K$) as a light source.

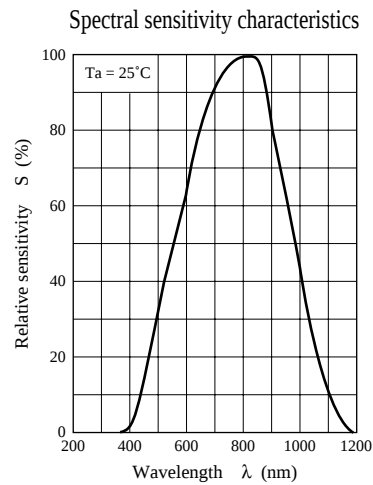
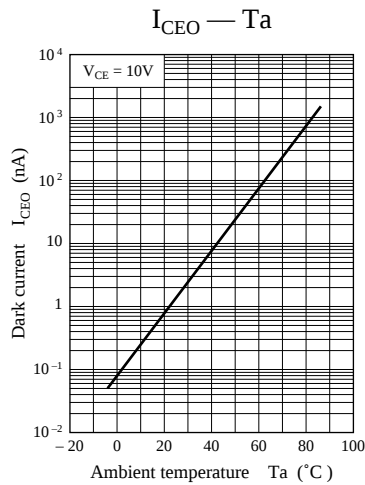
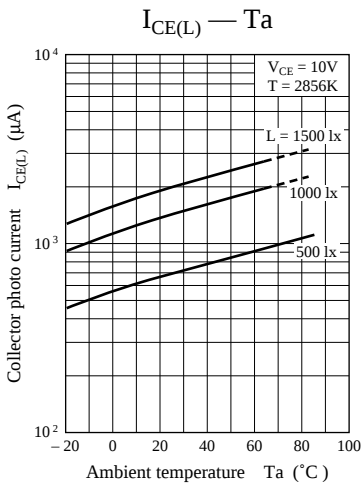
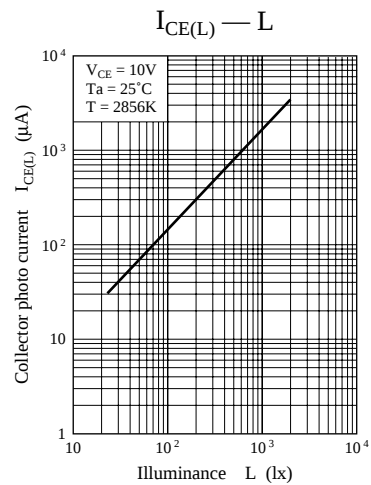
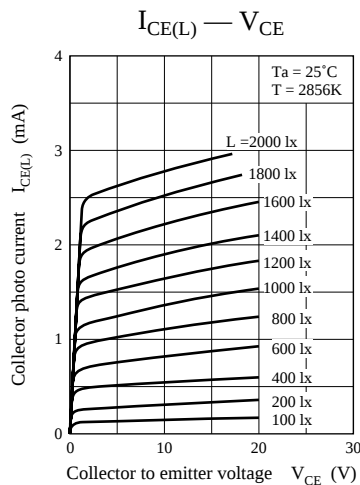
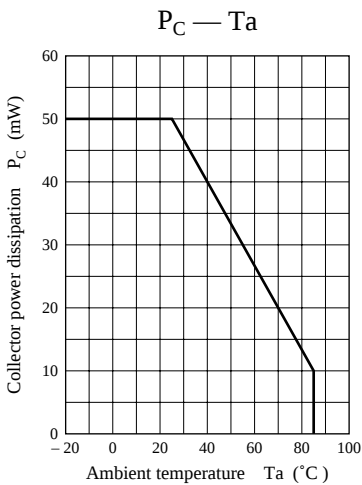
^{*2} Switching time measurement circuit



^{*3} $I_{CE(L)}$ Classifications

Class	Q	R	S	T	U
$I_{CE(L)} (\mu A)$	1050 to 1350	1260 to 1580	1480 to 1860	1730 to 2180	2030 to 2560
Color Indication	Brown	Yellow	Pink	Black	Red





Directivity characteristics

